

CMXESD70-4**SURFACE MOUNT SILICON
LOW CAPACITANCE
ESD PROTECTION
4-LINE DIODE ARRAY**www.centrasemi.com**SOT-26 CASE****DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMXESD70-4 is a 4-line silicon diode array packaged in the SOT-26 surface mount case. This device, with its low capacitance, is designed to protect four high speed data or transmission lines from over-voltage transients and ESD damage.

MARKING CODE: CTV70**FEATURES:**

- ESD protection: 8kV Contact; 15kV Air (IEC61000-4-2: Level 4)
- Low capacitance
- Protects four I/O lines
- Protects supply voltage rail

APPLICATIONS:

- USB 2.0 power and data line protection
- HDMI
- DVI
- Ethernet ports

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Peak Repetitive Reverse Voltage
Continuous Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$
Peak Forward Surge Current, $t_p=1.0\text{s}$
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL		UNITS
V_{RRM}	70	V
V_R	70	V
I_F	200	mA
I_{FRM}	450	mA
I_{FSM}	2.0	A
I_{FSM}	0.5	A
T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
θ_{JA}	556	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

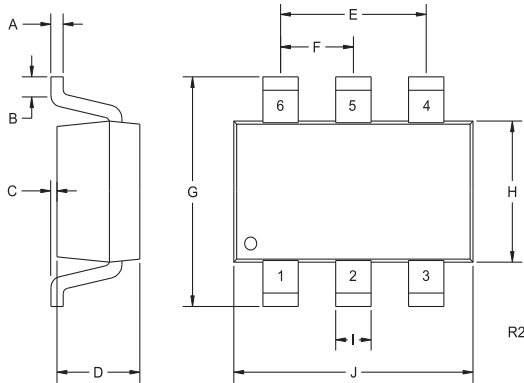
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=3.3\text{V}$		12	30	nA
I_R	$V_R=70\text{V}$		0.03	1.0	μA
I_R	$V_R=70\text{V}, T_J=150^\circ\text{C}$		55	100	μA
BV_R	$I_R=100\mu\text{A}$	70			V
V_F	$I_F=1.0\text{mA}$		0.61	0.715	V
V_F	$I_F=10\text{mA}$		0.74	0.855	V
V_F	$I_F=50\text{mA}$		0.88	1.0	V
V_F	$I_F=150\text{mA}$		1.07	1.25	V
C_J	$V_R=0\text{V}, f=1.0\text{MHz}$ (I/O to I/O)		0.45	0.9	pF
C_J	$V_R=0\text{V}, f=1.0\text{MHz}$ (I/O to GND)		0.77	1.0	pF

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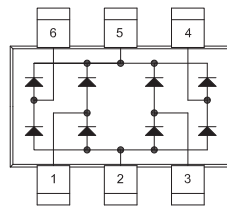
SOT-26 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

PIN CONFIGURATION

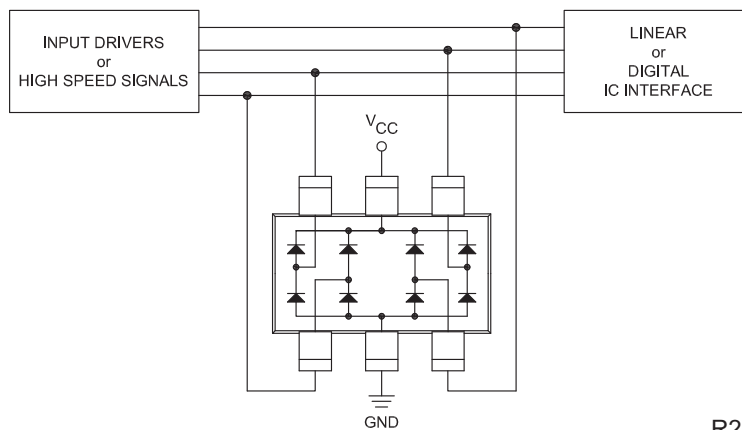


LEAD CODE:

- 1) I/O 1
- 2) Ground
- 3) I/O 2
- 4) I/O 3
- 5) Supply Voltage (V_{CC})
- 6) I/O 4

MARKING CODE: CTV70

Theory of operation: In this configuration, when the transient voltage exceeds the sum of the diode forward voltage drop (V_F), plus the supply voltage (V_{CC}), the diode will direct the surge to the supply, thereby protecting the high speed data line.



R2 (9-January 2013)

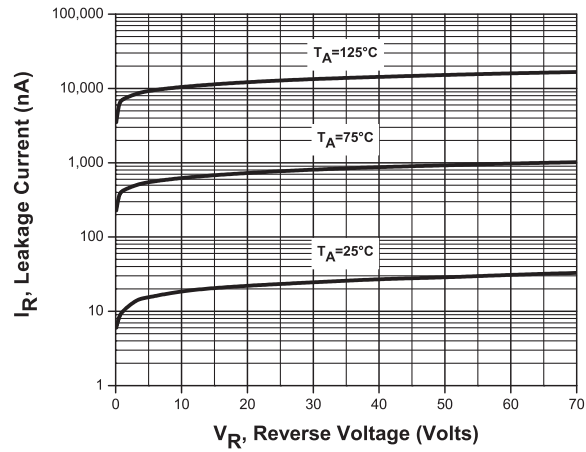
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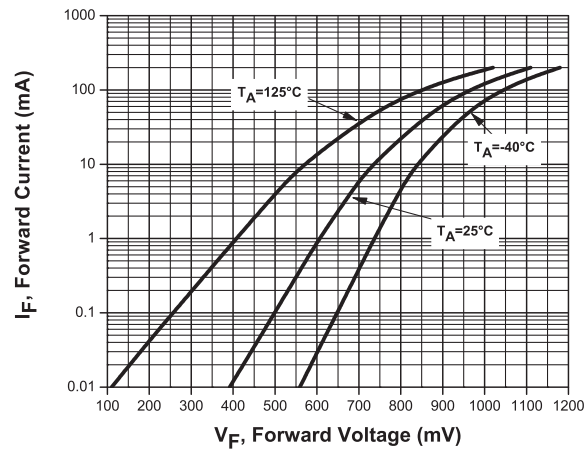


TYPICAL ELECTRICAL CHARACTERISTICS

Typical Per Diode Leakage Current



Typical Per Diode Forward Voltage



R2 (9-January 2013)